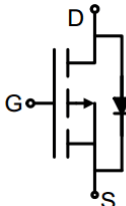
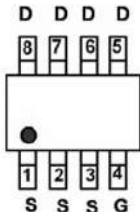


P-Channel Enhancement Mode Power MOSFET

Description The G16P03S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications. General Features ● V_{DS} -30V ● I_D (at $V_{GS} = -10V$) -16A ● $R_{DS(ON)}$ (at $V_{GS} = -10V$) < 12mΩ ● $R_{DS(ON)}$ (at $V_{GS} = -4.5V$) < 18mΩ ● 100% Avalanche Tested ● RoHS Compliant Application ● Power switch ● DC/DC converters		 Schematic diagram  Marking and pin assignment  SOP-8	
Device	Package	Marking	Packaging
G16P03S	SOP-8	G16P03	4000pcs/Reel

Absolute Maximum Ratings $T_C = 25^{\circ}C$, unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Continuous Drain Current	I_D	-16	A
Pulsed Drain Current (note1)	I_{DM}	-64	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	3	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^{\circ}C$

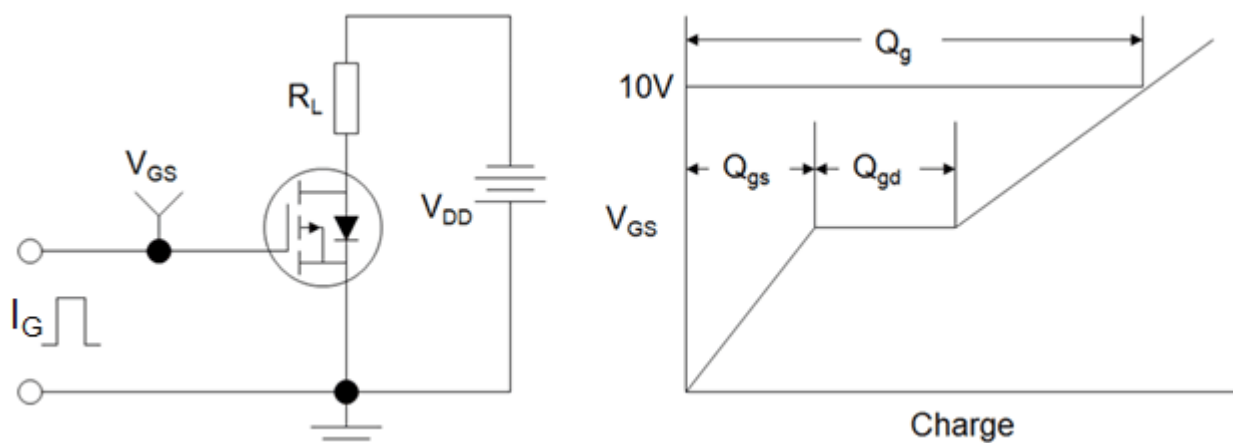
Thermal Resistance			
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	41	$^{\circ}C/W$

Specifications T _j = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V	--	--	-100	nA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1	-1.5	-2.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -10V, I _D = -10A	--	9.9	12	mΩ
		V _{GS} = -4.5V, I _D = -7A	--	14	18	
Forward Transconductance	g _{FS}	V _{DS} =-15V,I _D =-3A	--	42	--	S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -15V, f = 1.0MHz	--	2800	--	pF
Output Capacitance	C _{oss}		--	340	--	
Reverse Transfer Capacitance	C _{rss}		--	335	--	
Total Gate Charge	Q _g	V _{DD} = -15V, I _D = -10A, V _{GS} = -10V	--	35	--	nC
Gate-Source Charge	Q _{gs}		--	5.7	--	
Gate-Drain Charge	Q _{gd}		--	8.8	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = -15V, I _D = -10A, R _G = 1Ω	--	11	--	ns
Turn-on Rise Time	t _r		--	7.5	--	
Turn-off Delay Time	t _{d(off)}		--	43.5	--	
Turn-off Fall Time	t _f		--	17.5	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	-16	A
Body Diode Voltage	V _{SD}	T _j = 25°C, I _{SD} = -10A, V _{GS} = 0V	--	--	-1.2	V
Reverse Recovery Time	T _{rr}	I _S = 10A, V _{GS} = 0V di/dt=500A/us	--	13.3	--	ns

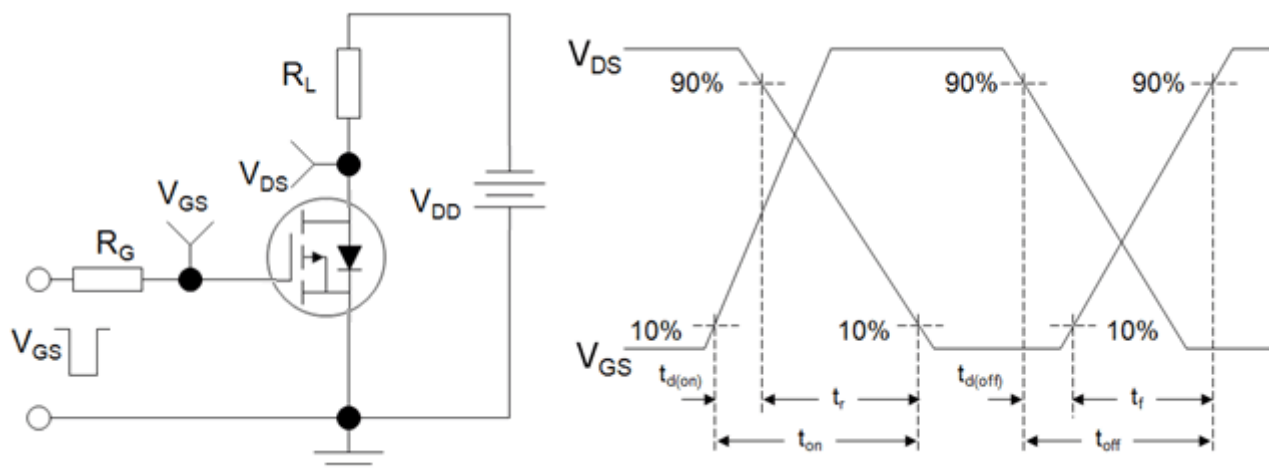
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G

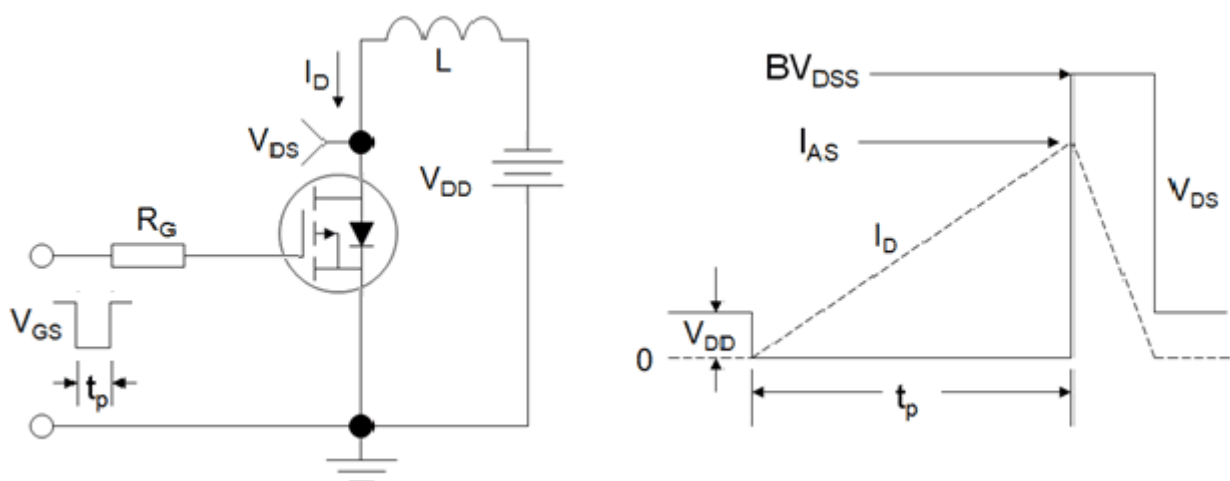
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

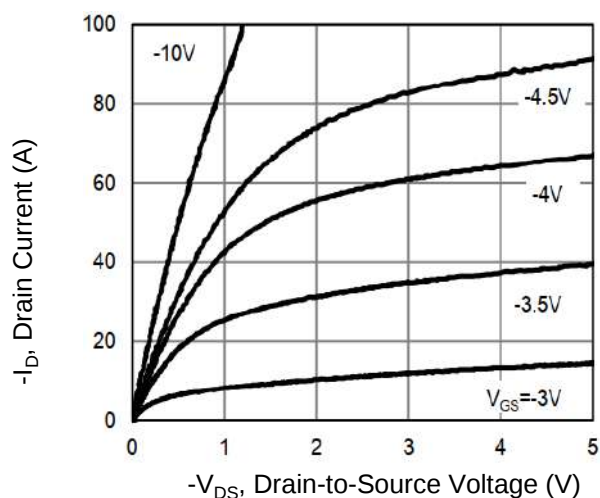


Figure 2. Transfer Characteristics

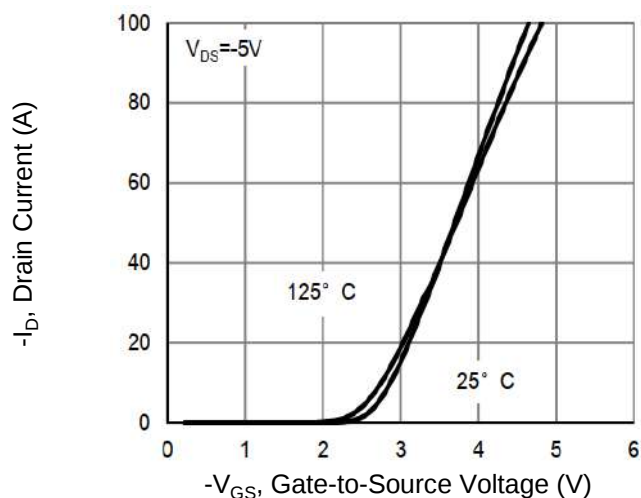


Figure 3. $R_{DS(on)}$ vs V_{GS}

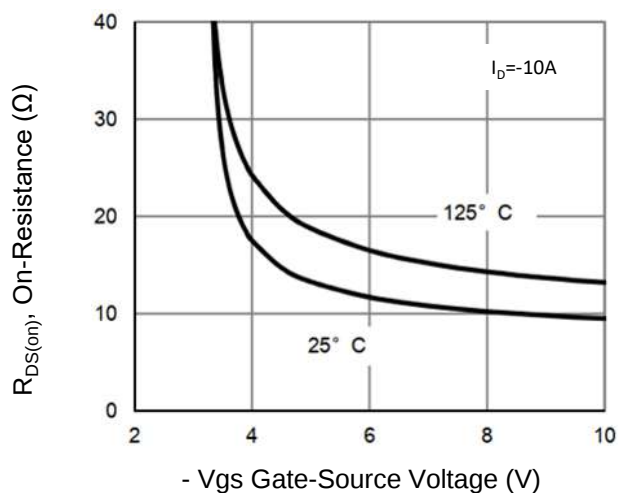


Figure 4. Gate Charge

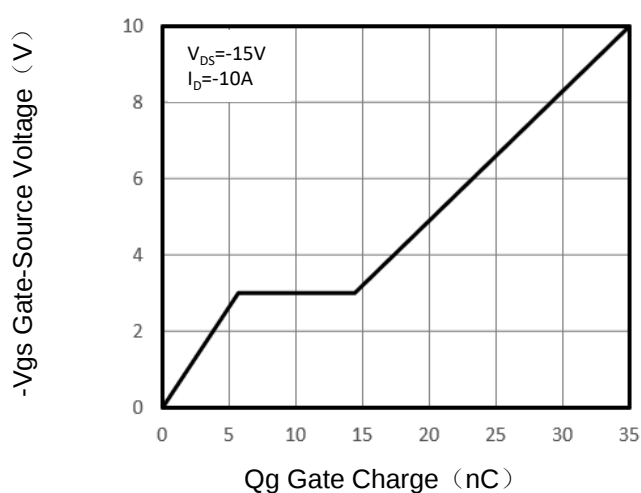


Figure 5. Capacitance vs V_{DS}

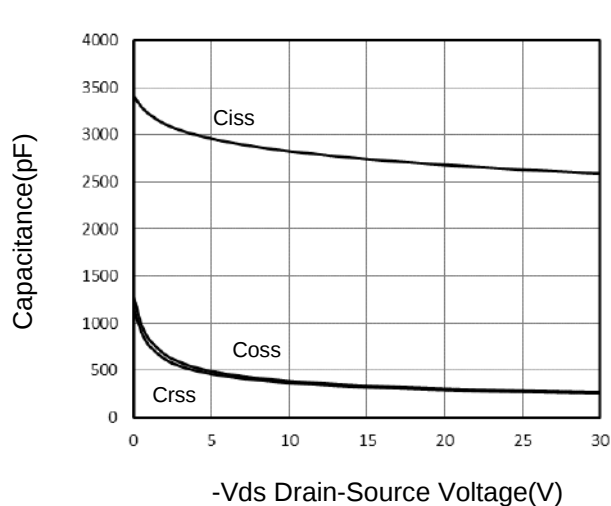
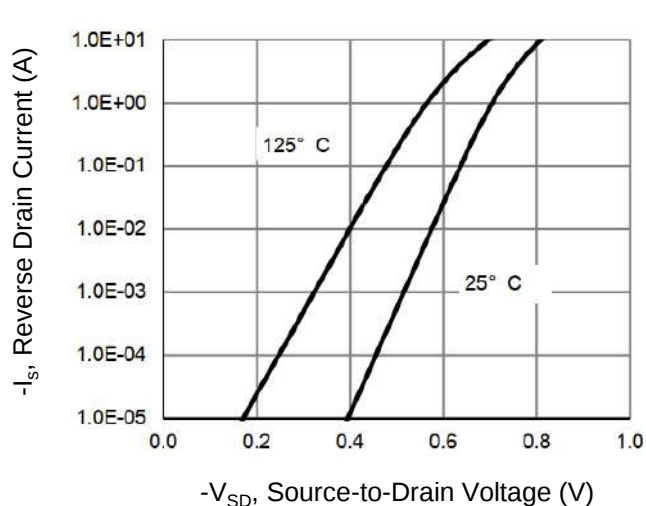


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

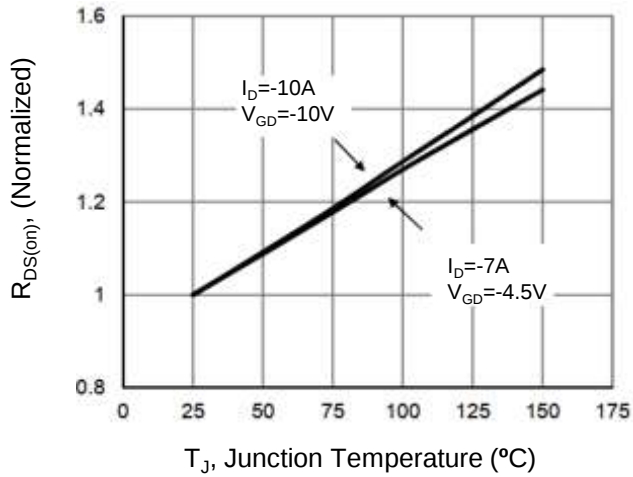


Figure 10. Safe Operation Area

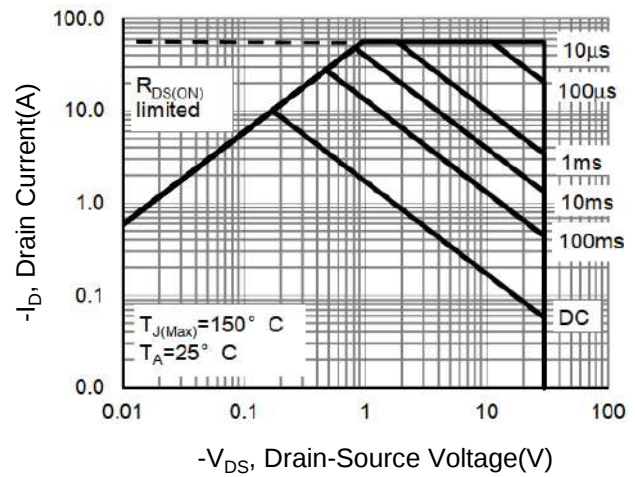
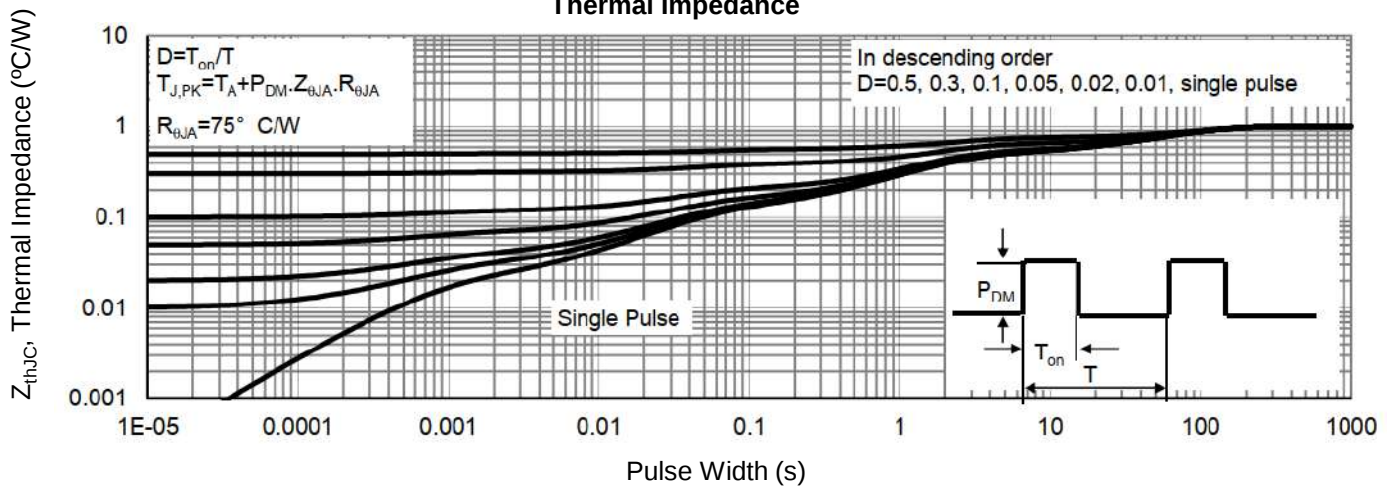
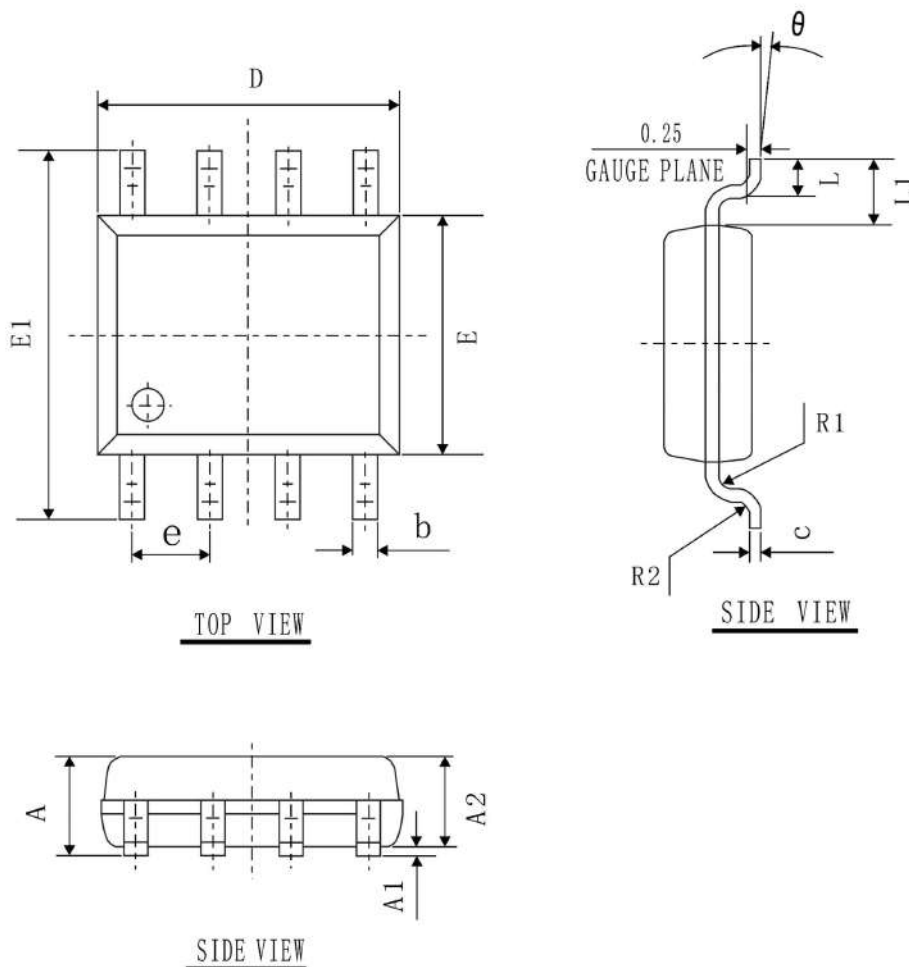


Figure 9. Normalized Maximum Transient Thermal Impedance



SOP-8 Package Information



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	1.40	1.60	1.80
A1	0.05	0.15	0.25
A2	1.35	1.45	1.55
b	0.30	0.40	0.50
c	0.153	0.203	0.253
D	4.80	4.90	5.00
E	3.80	3.90	4.00
E1	5.80	6.00	6.20
L	0.45	0.70	1.00
θ	2°	4°	6°
L1	1.04 REF		
e	1.27 BSC		
R1	0.07 TYP		
R2	0.07 TYP		